

2SK3512-01L,S,SJ

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FUJI
ELECTRIC

FUJI POWER MOSFET Super FAP-G Series

N-CHANNEL SILICON POWER MOSFET

■ Features

High speed switching
Low on-resistance
No secondary breakdown
Low driving power
Avalanche-proof

■ Applications

Switching regulators
UPS (Uninterruptible Power Supply)
DC-DC converters

■ Maximum ratings and characteristicAbsolute maximum ratings

● (Tc=25°C unless otherwise specified)

Item	Symbol	Ratings	Unit
Drain-source voltage	V _{DS}	500	V
Continuous drain current	I _D	±12	A
Pulsed drain current	I _D (puls)	±48	A
Gate-source voltage	V _{GS}	±30	V
Repetitive or non-repetitive	I _{AR} *2	12	A
Maximum Avalanche Energy	E _{AS} *1	217	mJ
Maximum Drain-Source dV/dt	dV _{DS} /dt *4	20	kV/μs
Peak Diode Recovery dV/dt	dV/dt *3	5	kV/μs
Max. power dissipation	P _D	Ta=25°C	W
		Tc=25°C	
Operating and storage temperature range	T _{ch}	+150	°C
	T _{stg}	-55 to +150	°C

*1 L=2.77mH, V_{CC}=50V *2 T_{ch}≤150°C *3 I_F≤-I_D, -di/dt=50A/μs, V_{CC}≤BV_{DSS}, T_{ch}≤150°C

*4 V_{DS}≤500V

● Electrical characteristics (Tc =25°C unless otherwise specified)

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain-source breakdown voltage	V _{(BR)DSS}	I _D =250μA V _{GS} =0V	500			V
Gate threshold voltage	V _{GS(th)}	I _D =250μA V _{DS} =V _{GS}	3.0		5.0	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =500V V _{GS} =0V V _{DS} =400V V _{GS} =0V			25 250	μA
Gate-source leakage current	I _{GSS}	V _{GS} =±30V V _{DS} =0V		10	100	nA
Drain-source on-state resistance	R _{DS(on)}	I _D =6A V _{GS} =10V		0.40	0.52	Ω
Forward transconductance	g _{fs}	I _D =6A V _{DS} =25V	5.5	11		S
Input capacitance	C _{iss}	V _{DS} =25V		1200	1800	pF
Output capacitance	C _{oss}	V _{GS} =0V		140	210	pF
Reverse transfer capacitance	C _{rss}	f=1MHz		6.0	9.0	pF
Turn-on time t _{on}	t _{d(on)} t _r	V _{CC} =300V I _D =6A V _{GS} =10V		17 15	26 23	ns
Turn-off time t _{off}	t _{d(off)} t _f	R _{GS} =10 Ω		34 7	51 11	ns
Total Gate Charge	Q _G	V _{CC} =250V		30	45	nC
Gate-Source Charge	Q _{GS}	I _D =12A		11	16.5	nC
Gate-Drain Charge	Q _{GD}	V _{GS} =10V		10	15	nC
Avalanche capability	I _{AV}	L=2.77mH T _{ch} =25°C	12			A
Diode forward on-voltage	V _{SD}	I _F =12A V _{GS} =0V T _{ch} =25°C		1.00	1.50	V
Reverse recovery time	t _{rr}	I _F =12A V _{GS} =0V		0.7		μs
Reverse recovery charge	Q _{rr}	-di/dt=100A/μs T _{ch} =25°C		4.5		μC

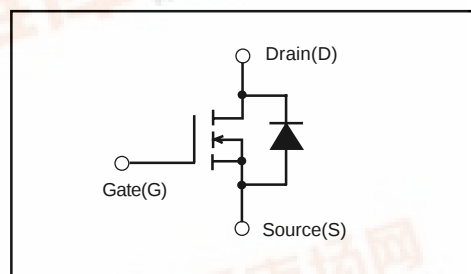
● Thermal characteristics

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	R _{th(ch-c)}	channel to case			1.32	°C/W

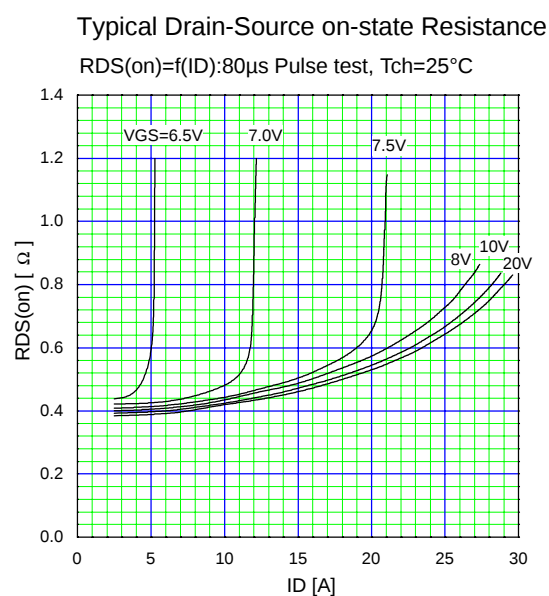
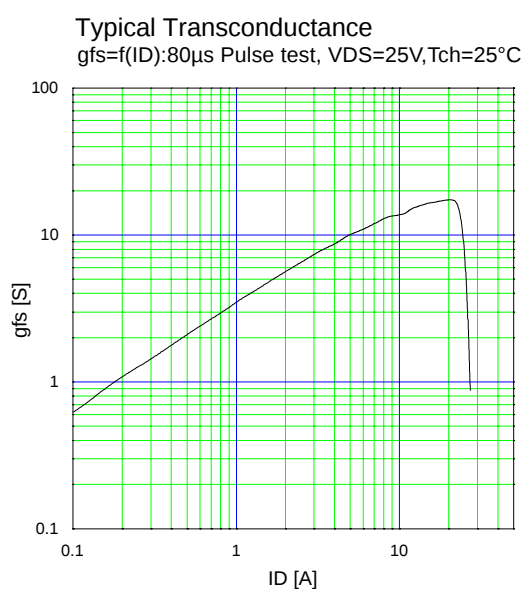
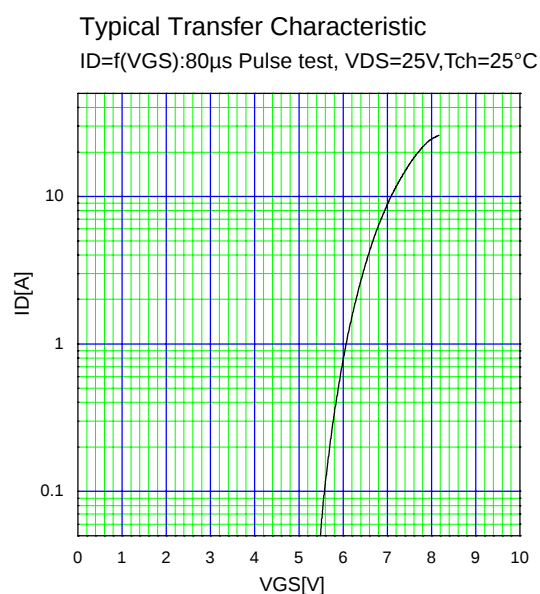
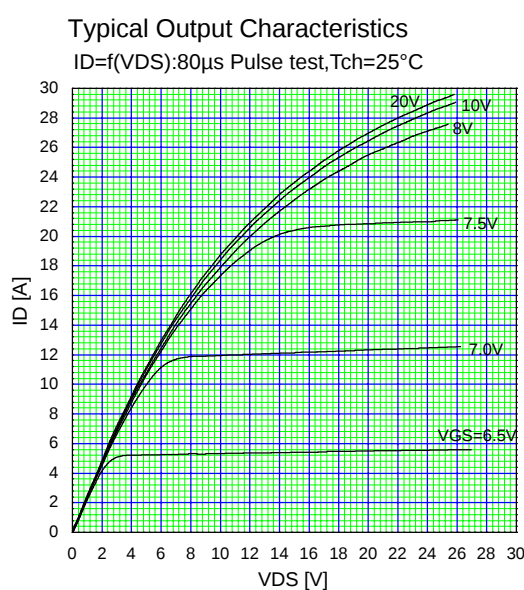
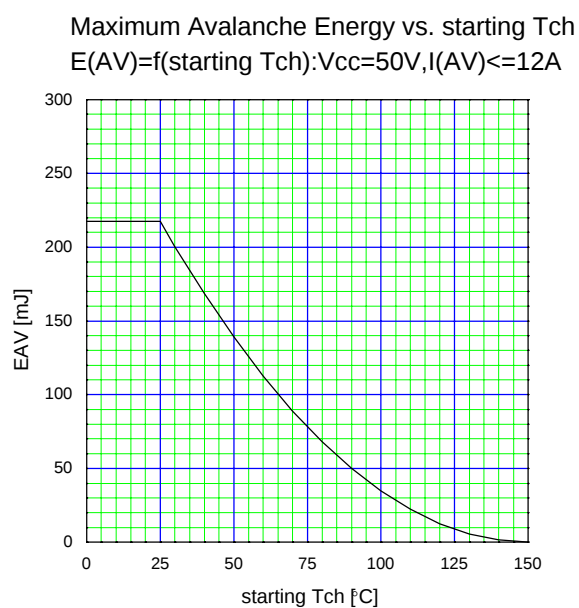
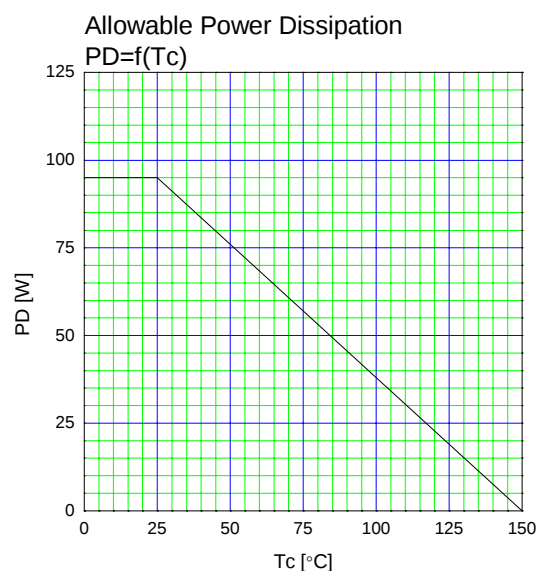
■ Outline Drawings



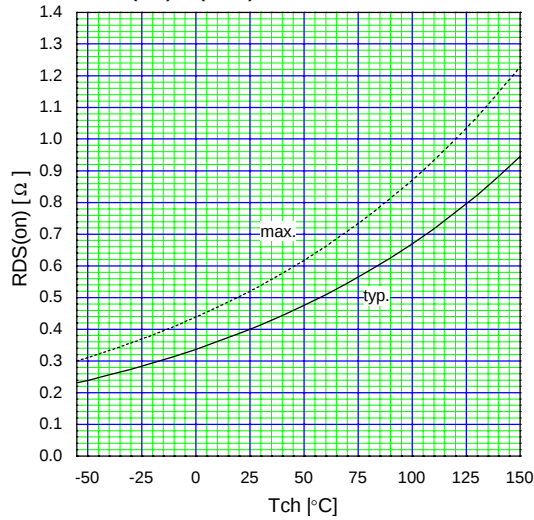
■ Equivalent circuit schematic



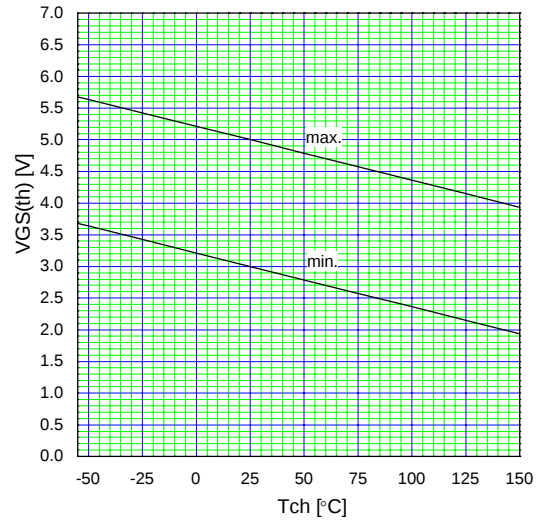
■ Characteristics



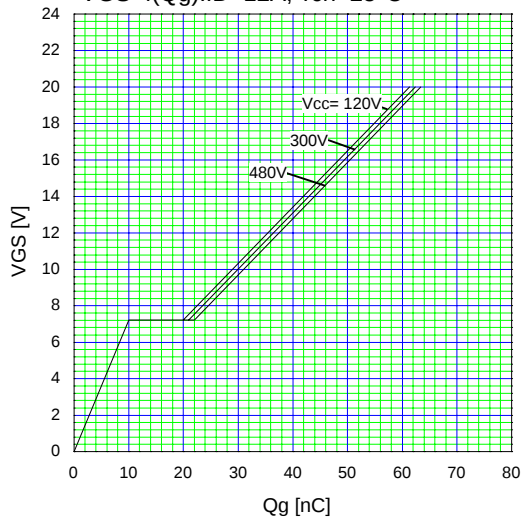
Drain-Source On-state Resistance
 $R_{DS(on)} = f(T_{ch}): I_D = 6A, V_{GS} = 10V$



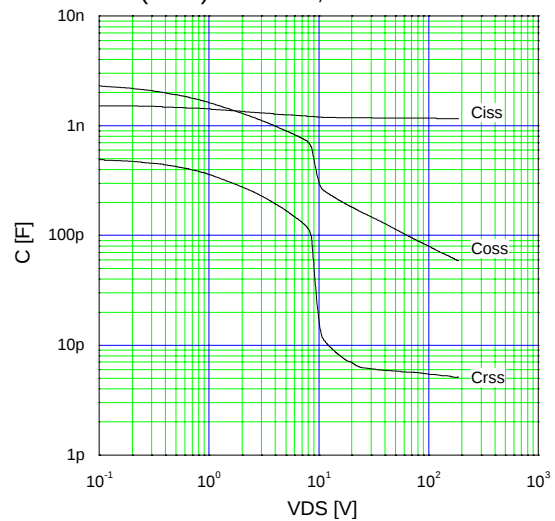
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)} = f(T_{ch}): V_{DS} = V_{GS}, I_D = 250\mu A$



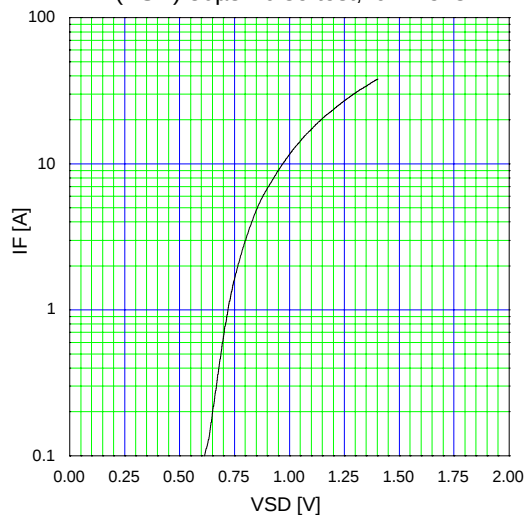
Typical Gate Charge Characteristics
 $V_{GS} = f(Q_g): I_D = 12A, T_{ch} = 25^{\circ}C$



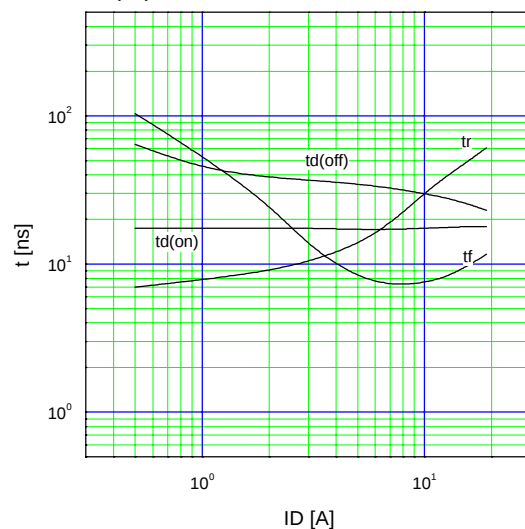
Typical Capacitance
 $C = f(V_{DS}): V_{GS} = 0V, f = 1MHz$

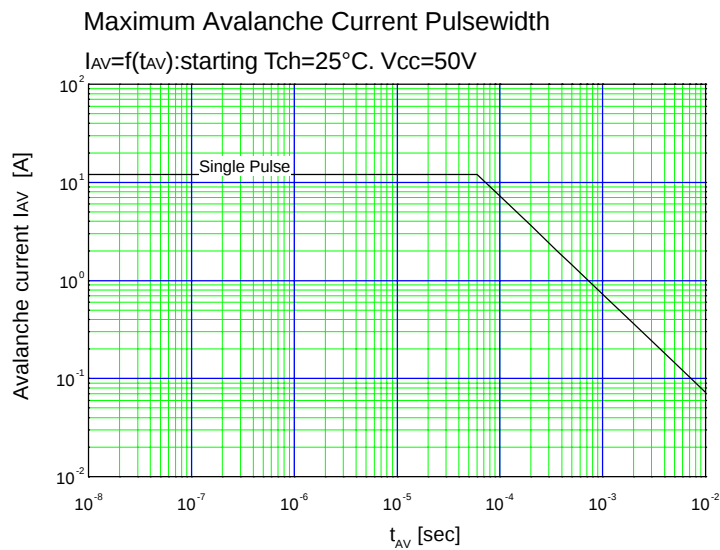
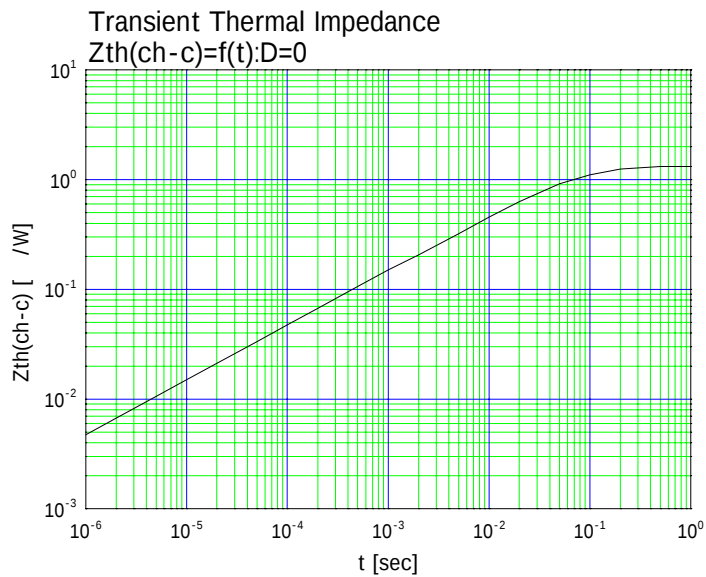


Typical Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD}): 80\mu s$ Pulse test, $T_{ch} = 25^{\circ}C$



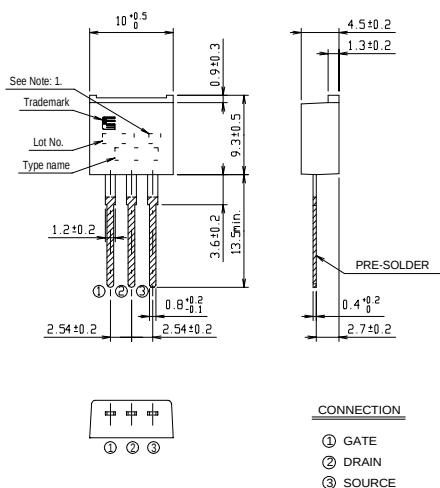
Typical Switching Characteristics vs. I_D
 $t = f(I_D): V_{CC} = 300V, V_{GS} = 10V, R_G = 10\Omega$



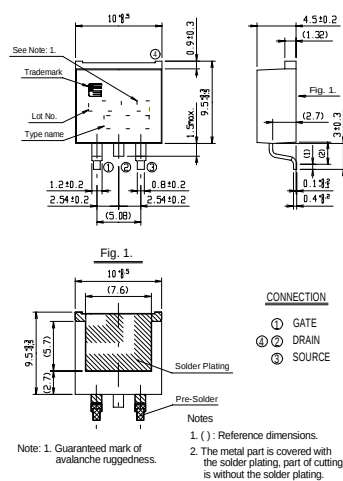


Outline Drawings (mm)

Type(L)



Type(S)



Type(SJ)

